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**01-maj-2018**

**Nadomešča:**
**SIST EN 60749-26:2014**

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**Polprevodniški elementi - Metode za mehansko in klimatsko preskušanje - 26. del: Preskušanje občutljivosti na elektrostatično razelektritev (ESD) - Model človeškega telesa (HBM) (IEC 60749-26:2018)**

Semiconductor devices - Mechanical and climatic test methods - Part 26: Electrostatic discharge (ESD) sensitivity testing - Human body model (HBM) (IEC 60749-26:2018)

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Halbleiterbauelemente - Mechanische und klimatische Prüfverfahren - Teil 26: Prüfung der Empfindlichkeit gegen elektrostatische Entladungen (ESD) - Human Body Model (HBM) (IEC 60749-26:2018)

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Dispositifs à semiconducteurs - Méthodes d'essais mécaniques et climatiques - Partie 26: Essai de sensibilité aux décharges électrostatiques (DES) - Modèle du corps humain (HBM) (IEC 60749-26:2018)

**Ta slovenski standard je istoveten z:** **EN IEC 60749-26:2018**

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**ICS:**

| | | |
|---|---|---|
| 31.080.01 | Polprevodniški elementi (naprave) na splošno | Semiconductor devices in general |

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NORME EUROPÉENNE

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# EN IEC 60749-26

March 2018

ICS 31.080.01

Supersedes EN 60749-26:2014

English Version

## Semiconductor devices - Mechanical and climatic test methods - Part 26: Electrostatic discharge (ESD) sensitivity testing - Human body model (HBM) (IEC 60749-26:2018)

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(IEC 60749-26:2018)

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## European foreword

The text of document 47/2438/FDIS, future edition 4 of IEC 60749-26, prepared by IEC/TC 47 "Semiconductor devices" was submitted to the IEC-CENELEC parallel vote and approved by CENELEC as EN IEC 60749-26:2018.

The following dates are fixed:

| | | |
|---|---|---|
| • latest date by which the document has to be implemented at national level by publication of an identical national standard or by endorsement | (dop) | 2018-11-19 |
| • latest date by which the national standards conflicting with the document have to be withdrawn | (dow) | 2021-02-19 |

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In the official version, for Bibliography, the following notes have to be added for the standards indicated:

| | | |
|---|---|---|
| IEC 60749 (series) | NOTE | Harmonized as EN 60749 (series). |
| IEC 60749-27 | NOTE | Harmonized as EN 60749-27. |

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# IEC 60749-26

Edition 4.0 2018-01

# INTERNATIONAL STANDARD

# NORME INTERNATIONALE

## Semiconductor devices – Mechanical and climatic test methods – Part 26: Electrostatic discharge (ESD) sensitivity testing – Human body model (HBM)

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## Dispositifs à semiconducteurs – Méthodes d'essais mécaniques et climatiques – Partie 26: Essai de sensibilité aux décharges électrostatiques (DES) – Modèle du corps humain (HBM)

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# SEMICONDUCTOR DEVICES – MECHANICAL AND CLIMATIC TEST METHODS –

## Part 26: Electrostatic discharge (ESD) sensitivity testing – Human body model (HBM)

## FOREWORD

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International Standard IEC 60749-26 has been prepared by IEC technical committee 47: Semiconductor devices in collaboration with technical committee 101: Electrostatics.

This fourth edition cancels and replaces the third edition published in 2013. This edition constitutes a technical revision. This standard is based upon ANSI/ESDA/JEDEC JS-001-2014. It is used with permission of the copyright holders, ESD Association and JEDEC Solid state Technology Association.

This edition includes the following significant technical changes with respect to the previous edition:

a) a new subclause relating to HBM stressing with a low parasitic simulator is added, together with a test to determine if an HBM simulator is a low parasitic simulator;

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b) a new subclause is added for cloned non-supply pins and a new annex is added for testing cloned non-supply pins.

The text of this International Standard is based on the following documents:

| FDIS | Report on voting |
|---|---|
| 47/2438/FDIS | 47/2454/RVD |

Full information on the voting for the approval of this International Standard can be found in the report on voting indicated in the above table.

This document has been drafted in accordance with the ISO/IEC Directives, Part 2.

A list of all parts in the IEC 60749 series, published under the general title *Semiconductor devices – Mechanical and climatic test methods*, can be found on the IEC website.

The committee has decided that the contents of this document will remain unchanged until the stability date indicated on the IEC website under "http://webstore.iec.ch" in the data related to the specific document. At this date, the document will be

- reconfirmed,
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# SEMICONDUCTOR DEVICES – MECHANICAL AND CLIMATIC TEST METHODS –

# Part 26: Electrostatic discharge (ESD) sensitivity testing – Human body model (HBM)

## 1 Scope

This part of IEC 60749 establishes the procedure for testing, evaluating, and classifying components and microcircuits according to their susceptibility (sensitivity) to damage or degradation by exposure to a defined human body model (HBM) electrostatic discharge (ESD).

The purpose of this document is to establish a test method that will replicate HBM failures and provide reliable, repeatable HBM ESD test results from tester to tester, regardless of component type. Repeatable data will allow accurate classifications and comparisons of HBM ESD sensitivity levels.

ESD testing of semiconductor devices is selected from this test method, the machine model (MM) test method (see IEC 60749-27) or other ESD test methods in the IEC 60749 series. Unless otherwise specified, this test method is the one selected.

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## 2 Normative references

The following documents are referred to in the text in such a way that some or all of their content constitutes requirements of this document. For dated references, only the edition cited applies. For undated references, the latest edition of the referenced document (including any amendments) applies.

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There are no normative references in this document.

## 3 Terms and definitions

For the purposes of this document, the following terms and definitions apply.

ISO and IEC maintain terminological databases for use in standardization at the following addresses:

- IEC Electropedia: available at http://www.electropedia.org/
- ISO Online browsing platform: available at http://www.iso.org/obp

**3.1**
**associated non-supply pin**
non-supply pin (typically an I/O pin) associated with a supply pin group

Note 1 to entry A non-supply pin is considered to be associated with a supply pin group if either:

a) the current from the supply pin group (i.e., VDDIO) is required for the function of the electrical circuit(s) (I/O driver) that connect(s) (high/low impedance) to that non-supply pin;

b) a parasitic path exists between non-supply and supply pin group (e.g., open-drain type non-supply pin to a VCC supply pin group that connects to a nearby N-well guard ring).

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**3.2**
**cloned non-supply (I/O) pin**
set of input, output or bidirectional pins using the same I/O cell and electrical schematic and sharing the same associated supply pin group(s) including ESD power clamp(s)

**3.3**
**component**
item such as a resistor, diode, transistor, integrated circuit or hybrid circuit

**3.4**
**component failure**
condition in which a tested component does not meet one or more specified static or dynamic data sheet parameters

**3.5**
**coupled non-supply pin pair**
two pins that have an intended direct current path (such as a pass gate or resistors, such as differential amplifier inputs, or low voltage differential signalling (LVDS) pins), including analogue and digital differential pairs and other special function pairs (e.g., D+/D-, XTALin/XTALout, RFin/RFout, TxP/TxN, RxP/RxN, CCP_DP/CCN_DN, etc.)

**3.6**
**data sheet parameters**
static and dynamic component performance data supplied by the component manufacturer or supplier

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**3.7**
**withstand voltage**
highest voltage level that does not cause device failure

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Note 1 to entry: The device passes all tested lower voltages (see failure window).

**3.8**
**failure window**
intermediate range of stress voltages that can induce failure in a particular device type, when the device type can pass some stress voltages both higher and lower than this range

Note 1 to entry: A component with a failure window can pass a 500 V test, fail a 1 000 V test and pass a 2 000 V test. The withstand voltage of such a device is 500 V.

**3.9**
**human body model electrostatic discharge**
**HBM ESD**
ESD event meeting the waveform criteria specified in this document, approximating the discharge from the fingertip of a typical human being to a grounded device

**3.10**
**HBM ESD tester**
HBM simulator
equipment that applies an HBM ESD to a component

**3.11**
$I_{ps}$
peak current value determined by the current at time $t_{max}$ on the linear extrapolation of the exponential current decay curve, based on the current waveform data over a 40 nanosecond period beginning at $t_{max}$

SEE: Figure 2 a).

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**3.12**
**$I_{psmax}$**
highest current value measured including the overshoot or ringing components due to internal test simulator RLC parasitics

SEE: Figure 2 a).

**3.13**
**no connect pin**
package interconnection that is not electrically connected to a die

EXAMPLE: Pin, bump, ball interconnection.

Note 1 to entry: There are some pins which are labelled as no connect, which are actually connected to the die and should not be classified as a no connect pin.

**3.14**
**non-socketed tester**
HBM simulator that makes contact to the device under test (DUT) pins (or balls, lands, bumps or die pads) with test probes rather than placing the DUT in a socket

**3.15**
**non-supply pin**
pin that is not categorized as a supply pin or no connect

Note 1 to entry This includes pins such as input, output, offset adjusts, compensation, clocks, controls, address, data, Vref pins and VPP pins on EPROM memory. Most non-supply pins transmit or receive information such as digital or analogue signals, timing, clock signals, and voltage or current reference levels.

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**3.16**
**package plane**
low impedance metal layer built into an IC package connecting a group of bumps or pins (typically power or ground)

Note 1 to entry: There may be multiple package planes (sometimes referred to as islands) for each power and ground group.

**3.17**
**pre-pulse voltage**
voltage occurring at the device under test (DUT) just prior to the generation of the HBM current pulse

SEE: Clause B.2.

**3.18**
**pulse generation circuit**
dual polarity pulse source circuit network that produces a human body discharge current waveform

Note 1 to entry The circuit network includes a pulse generator with its test equipment internal path up to the contact pad of the test fixture. This circuit is also referred to as dual polarity pulse source.

**3.19**
**ringing**
high frequency oscillation superimposed on a waveform

**3.20**
**shorted non-supply pin**
any non-supply pin (typically an I/O pin) that is metallically connected (typically $< 3\ \Omega$) on the chip or within the package to another non-supply pin (or set of non-supply pins)

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**3.21**
**socketed tester**
HBM simulator that makes contact to DUT pins (or balls, lands, bumps or die pads) using a DUT socket mounted on a test fixture board

**3.22**
**spurious current pulse**
small HBM shaped pulse that follows the main current pulse, and is typically defined as a percentage of $I_{psmax}$

**3.23**
**step-stress hardening**
ability of a component subjected to increasing ESD voltage stresses to withstand higher stress levels than a similar component not previously stressed

EXAMPLE: A component can fail at 1 000 V if subjected to a single stress, but fail at 3 000 V if stressed incrementally from 250 V.

**3.24**
**supply pin**
any pin that provides current to a circuit

Note 1 to entry: Supply pins typically transmit no information (such as digital or analogue signals, timing, clock signals, and voltage or current reference levels). For the purpose of ESD testing, power and ground pins are treated as supply pins.

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**3.25**
**test fixture board**
specialized circuit board, with one or more component sockets, which connects the DUT(s) to the HBM simulator

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**3.26**
$t_{max}$
time when $I_{ps}$ is at its maximum value ($I_{psmax}$)

SEE: Figure 2 a).

**3.27**
**trailing current pulse**
current pulse that occurs after the HBM current pulse has decayed

Note 1 to entry: A trailing current pulse is a relatively constant current often lasting for hundreds of microseconds.

SEE: Clause B.1.

**3.28**
**two-pin HBM tester**
low parasitic HBM simulator that tests DUTs in pin pairs where floating pins are not connected to the simulator thereby eliminating DUT-tester interactions from parasitic tester loading of floating pins

## 4 Apparatus and required equipment

### 4.1 Waveform verification equipment

All equipment used to evaluate the tester shall be calibrated in accordance with the manufacturer's recommendation. This includes the oscilloscope, current transducer and high voltage resistor load. Maximum time between calibrations shall be one year. Calibration shall be traceable to national or international standards.

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Equipment capable of verifying the pulse waveforms defined in this standard test method includes, but is not limited to, an oscilloscope, evaluation loads and a current transducer.

### 4.2 Oscilloscope

A digital oscilloscope is recommended but analogue oscilloscopes are also permitted. In order to ensure accurate current waveform capture, the oscilloscope shall meet the following requirements:

a) minimum sensitivity of 100 mA per major division when used in conjunction with the current transducer specified in 4.4;

b) minimum bandwidth of 350 MHz;

c) for analogue scopes, minimum writing rate of one major division per nanosecond.

### 4.3 Additional requirements for digital oscilloscopes

Where a digital oscilloscope is used, the following additional requirements apply:

a) recommended channels: 2 or more;

b) minimum sampling rate: $10^9$ samples per second;

c) minimum vertical resolution: 8-bit;

d) minimum vertical accuracy: ± 2,5 %;

e) minimum time base accuracy: 0,01 %;

f) minimum record length: $10^3$ points.

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### 4.4 Current transducer (inductive current probe)

a) minimum bandwidth of 200 MHz;

b) peak pulse capability of 12 A;

c) rise time of less than 1 ns;

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d) capable of accepting a solid conductor as specified in 4.5;

e) provides an output voltage per signal current as required in 4.2

(this is usually between 1 mV/mA and 5 mV/mA.);

f) low-frequency 3 dB point below 10 kHz (e.g., Tektronix CT-2[1]) for measurement of decay constant $t_d$ (see 5.2.3.2, Table 1, and note below).

NOTE Results using a current probe with a low-frequency 3 dB point of 25 kHz (e.g., Tektronix CT-1[1]) to measure decay constant $t_d$ are acceptable if $t_d$ is found to be between 130 ns and 165 ns.

### 4.5 Evaluation loads

Two evaluation loads are necessary to verify the tester functionality:

a) Load 1: A solid 18 AWG to 24 AWG (non-US standard wire size 0,25 $mm^2$ to 0,75 $mm^2$ cross-section) tinned copper shorting wire as short as practicable to span the distance between the two farthest pins in the socket while passing through the current probe or long enough to pass through the current probe and contacted by the probes of the non-socketed tester.

b) Load 2: A (500 ± 5) Ω, minimum 4 000 V voltage rating.

[1] Tektronix CT-1 and CT-2 are the trade names of products supplied by Tektronix, Inc.

This information is given for the convenience of users of this document and does not constitute an endorsement by IEC of the products named. Equivalent products may be used if they can be shown to lead to the same results.